# Abstracts

## Simulation of Nonlinear Microwave FET Performance Using a Quasi-Static Model

*C. Rauscher and H.A. Willing. "Simulation of Nonlinear Microwave FET Performance Using a Quasi-Static Model." 1979 Transactions on Microwave Theory and Techniques 27.10 (Oct. 1979 [T-MTT]): 834-840.*

A technique is described for accurately predicting nonlinear performance of microwave GaAs field-effect transistors in arbitrary circuit embedding. The approach is based on a quasi-static device model which is derived from measured bias and frequency dependence of the small-signal device S parameters. Excellent agreement is demonstrated between experimental and predicted "load-pull" characteristics at X band.

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